ELECTRONICS, INC.
44 FARRAND STREET
BLOOMFIELD, NJ 07003
(973) 748–5089

NTE2559 (NPN) & NTE2560 (PNP)
Silicon Complementary Transistors
Darlington, Motor/Relay Driver

Absolute Maximum Ratings:

Collector–Base Voltage, V_{CBO} 120V
Collector–Emitter Voltage, V_{CEO} 120V
Emitter–Base Voltage, V_{EBO} 6V
Collector Current, I_C
  Continuous 16A
  Pulsed 26A
Base Current, I_B 1A
Collector Dissipation (T_{FL} = +25°C), P_D 3W
Operating Junction Temperature, T_J . . . . . +150°C
Storage Temperature Range, T_{stg} . . . . . –55° to +150°C

Electrical Characteristics: (T_A = +25°C unless otherwise specified)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector Cutoff Current	I_{CBO}	V_{CB} = 120V, I_E = 0	–	–	10	μA
Emitter Cutoff Current	I_{EBO}	V_{EB} = 6V, I_C = 0	–	–	10	mA
Collector–Emitter Breakdown Voltage	$V_{(BR)CEO}$	I_C = 10mA, R_{BE} = ∞	120	–	–	V
DC Current Gain	h_{FE}	V_{CE} = 4V, I_C = 8A	2000	–	–	
Collector–Emitter Saturation Voltage	$V_{CE(sat)}$	I_C = 8A, I_B = 16mA	–	–	1.5	V
Base–Emitter Saturation Voltage	$V_{BE(sat)}$	I_C = 8A, I_B = 16mA	–	–	2.5	V

Note 1. For NTE2560, the polarity is reversed.

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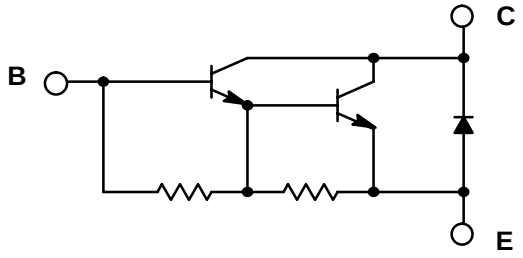

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